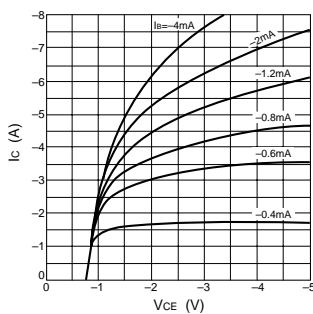


Electrical characteristics (Source: PNP transistor) (Ta=25°C)

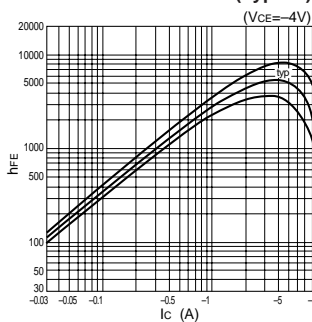
Symbol	Specification			Unit	Conditions
	min	typ	max		
ICBO			-10	μA	V _{CB} =-100V
IEBO			-10	mA	V _{EB} =-6V
V _{CEO}	-100			V	I _C =-10mA
h _{FE}	2000	5000	12000		V _{CE} =-4V, I _C =-3A
V _{CE(sat)}			-1.5	V	I _C =-3A, I _B =-6mA
V _{BE(sat)}			-2.2	V	
V _{FEC}			1.3	V	I _{FEC} =-1A
t _{rr}		2.0		μs	I _F =±100mA
t _{on}		0.6		μs	V _{CC} ≐-30V
t _{stg}		1.6		μs	I _C =-3A
t _f		0.5		μs	I _{B1} =-I _{B2} =-6mA
f _T		90		MHz	V _{CE} =-12V, I _E =1A
C _{ob}		100		pF	V _{CB} =-10V, f=1MHz

Characteristic curves (PNP)

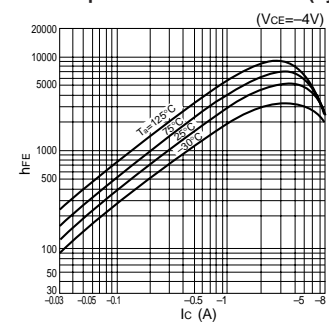
I_C-V_{CE} Characteristics (Typical)



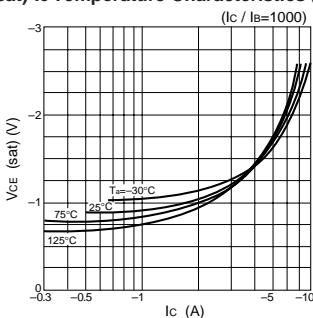
h_{FE}-I_C Characteristics (Typical)



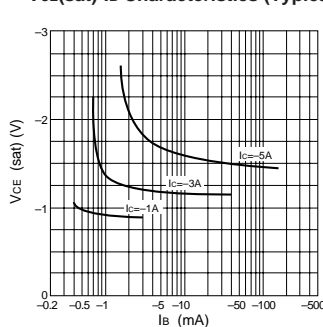
h_{FE}-I_C Temperature Characteristics (Typical)



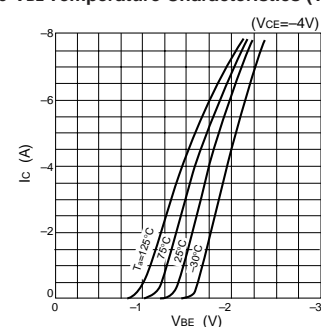
V_{CE(sat)}-I_C Temperature Characteristics (Typical)



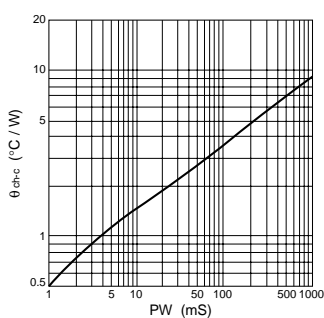
V_{CE(sat)}-I_B Characteristics (Typical)



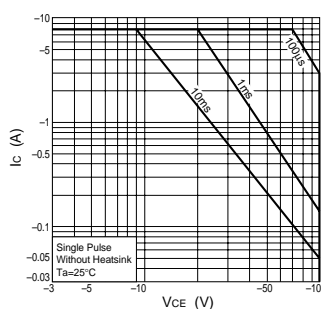
I_C-V_{BE} Temperature Characteristics (Typical)



θ_{J-a}-PW Characteristics



Safe Operating Area (SOA)



P_T-T_a Characteristics

